

BAS16TW

200mW Surface Mount Switching Diode - 100V

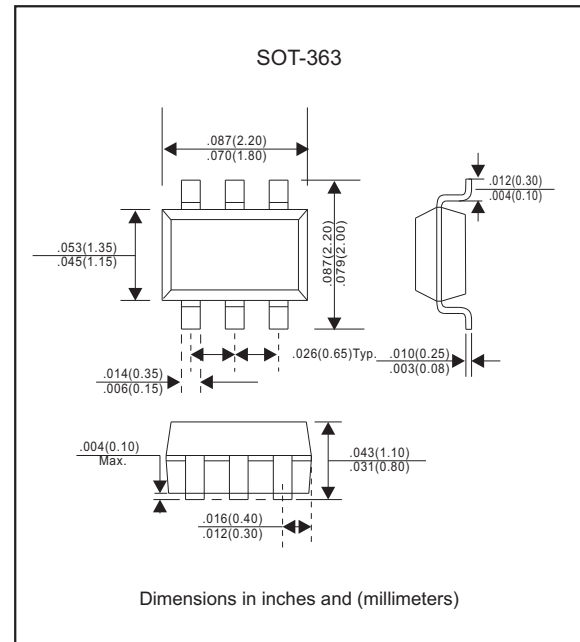
Features

- Fast speed switching.
- For general purpose switching application.
- High conductance.
- Easily connected as full wave bridge
- Silicon epitaxial planar chip.
- Lead-free parts meet RoHS requirements.
- Suffix "-H" indicates Halogen-free part, ex. BAS16TW-H.

Mechanical data

- Epoxy: UL94-V0 rated flame retardant
- Case : Molded plastic, SOT-363
- Terminals : Solder plated, solderable per MIL-STD-750, Method 2026
- Mounting Position : Any
- Weight : Approximated 0.006 gram

Package outline



Maximum ratings (AT $T_A=25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Value	Unit
Non-Repetitive Peak Reverse Voltage	V_{RM}	100	V
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	75	V
RMS Reverse Voltage	$V_{R(RMS)}$	53	V
Forward Continuous Current (Note 1)	I_{FM}	300	mA
Average Rectified Output Current (Note 1)	I_O	150	mA
Non-Repetitive Peak Forward Surge Current @ $t = 1.0\mu\text{s}$ @ $t = 1.0\text{s}$	I_{FSM}	2.0 1.0	A
Power Dissipation (Note 1)	P_D	200	mW
Thermal Resistance Junction to Ambient Air (Note 1)	$R_{\theta JA}$	625	$^\circ\text{C/W}$
Operating and Storage Temperature Range	T_J, T_{STG}	-65 to +150	$^\circ\text{C}$

Electrical Characteristics (AT $T_A=25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit	Test Condition
Reverse Breakdown Voltage (Note 2)	$V_{(BR)R}$	75		V	$I_R = 1\mu\text{A}$
Forward Voltage (Note 2)	V_F		0.715 0.855 1.0 1.25	V	$I_F = 1.0\text{mA}$ $I_F = 10\text{mA}$ $I_F = 50\text{mA}$ $I_F = 150\text{mA}$
Reverse Current (Note 2)	I_R		1.0 50 30 25	μA μA μA nA	$V_R = 75\text{V}$ $V_R = 75\text{V}, T_J = 150^\circ\text{C}$ $V_R = 25\text{V}, T_J = 150^\circ\text{C}$ $V_R = 20\text{V}$
Total Capacitance	C_T		2.0	pF	$V_R = 0\text{V}, f = 1.0\text{MHz}$
Reverse Recovery Time	t_{rr}		4.0	ns	$I_F = I_R = 10\text{mA}$, $I_{rr} = 0.1 \times I_R, R_L = 100\Omega$

- Notes:
1. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at <http://www.diodes.com/datasheets/ap02001.pdf>.
 2. Short duration test pulse used to minimize self-heating effect.

Rating and characteristic curves for each diode(BAS16TW)

Figure 1. Forward Voltage

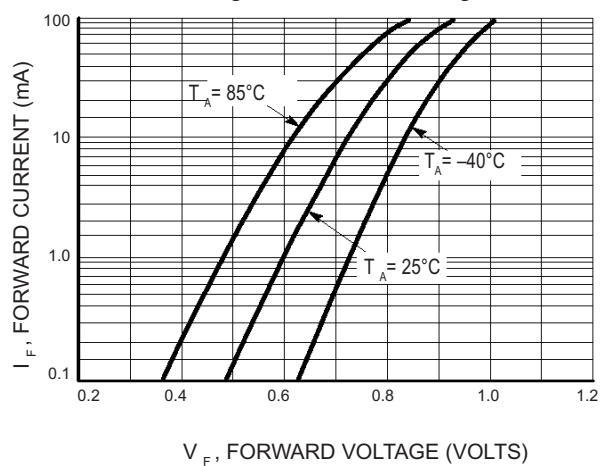


Figure 2. Leakage Current

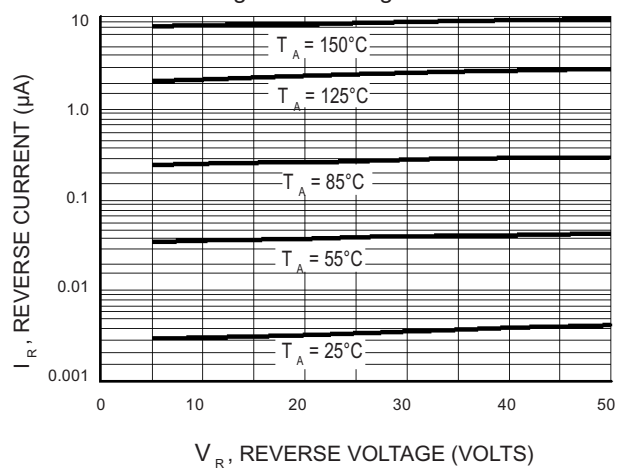
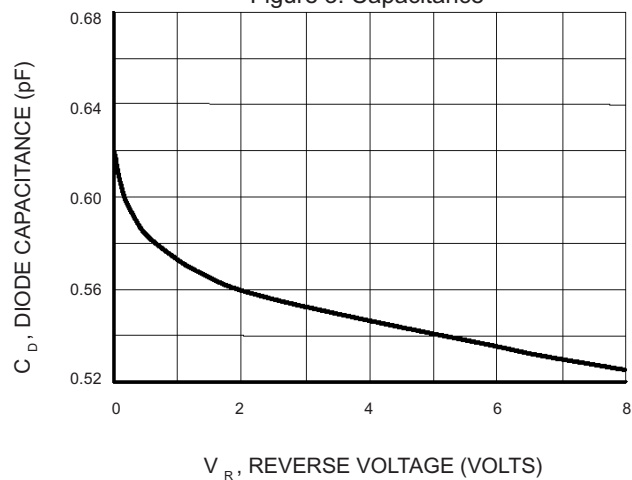
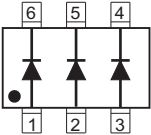


Figure 3. Capacitance



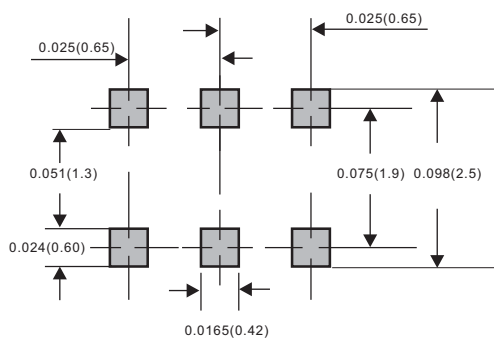
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Pinning information

Type number	Marking code	Symbol
BAS16TW	KA2	

Suggested solder pad layout

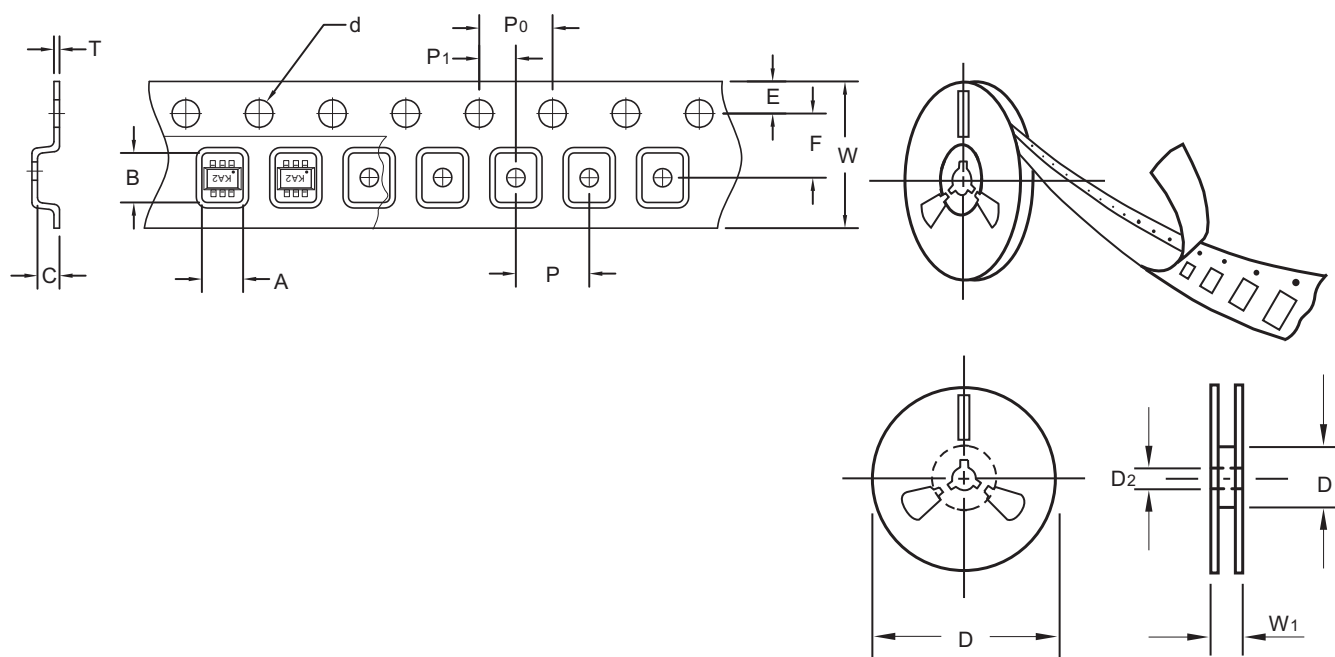
SOT-363



Dimensions in inches and (millimeters)

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Packing information



unit:mm

Item	Symbol	Tolerance	SOT-363
Carrier width	A	0.1	2.36
Carrier length	B	0.1	2.40
Carrier depth	C	0.1	1.20
Sprocket hole	d	0.1	1.50
13" Reel outside diameter	D	2.0	-
13" Reel inner diameter	D ₁	min	-
7" Reel outside diameter	D	2.0	178.00
7" Reel inner diameter	D ₁	min	62.00
Feed hole diameter	D ₂	0.5	13.00
Sprocket hole position	E	0.1	1.75
Punch hole position	F	0.1	3.50
Punch hole pitch	P	0.1	4.00
Sprocket hole pitch	P ₀	0.1	4.00
Embossment center	P ₁	0.1	2.00
Overall tape thickness	T	0.1	0.23
Tape width	W	0.3	8.00
Reel width	W ₁	1.0	11.40

Note: Devices are packed in accordance with EIA standard RS-481-A and specifications listed above.

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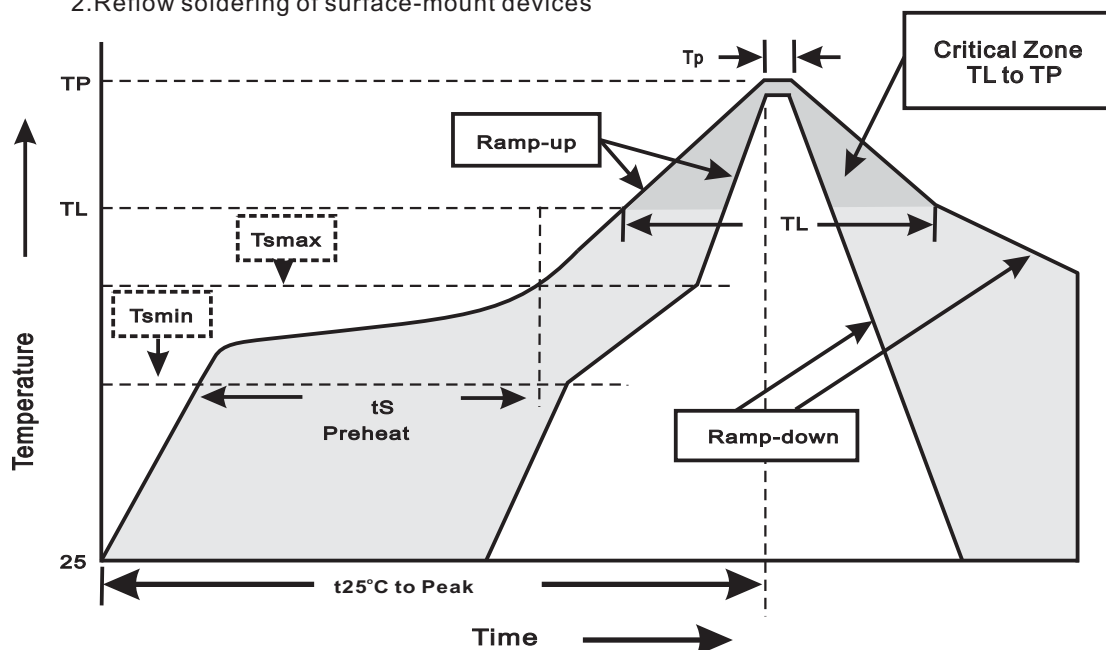
Reel packing

PACKAGE	REEL SIZE	REEL (pcs)	COMPONENT SPACING (m/m)	BOX (pcs)	INNER BOX (m/m)	REEL DIA, (m/m)	CARTON SIZE (m/m)	CARTON (pcs)	APPROX. GROSS WEIGHT (kg)
SOT-363	7"	3000	4.0	30,000	183*183*123	178	382*262*387	240,000	9.50

Suggested thermal profiles for soldering processes

1.Storage environment: Temperature=5°C~40°C Humidity=55%±25%

2.Reflow soldering of surface-mount devices



3.Reflow soldering

Profile Feature	Soldering Condition
Average ramp-up rate(T_L to T_P)	$<3^{\circ}\text{C}/\text{sec}$
Preheat -Temperature Min(T_{5min}) -Temperature Max(T_{5max}) -Time(min to max)(t_S)	150°C 200°C 60~120sec
T_{5max} to T_L -Ramp-upRate	$<3^{\circ}\text{C}/\text{sec}$
Time maintained above: -Temperature(T_L) -Time(t_L)	217°C 60~260sec
Peak Temperature(T_P)	255°C-0/+5°C
Time within 5°C of actual Peak Temperature(t_P)	10~30sec
Ramp-down Rate	$<6^{\circ}\text{C}/\text{sec}$
Time 25°C to Peak Temperature	$<6\text{minutes}$

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High reliability test capabilities

Item Test	Conditions	Reference
1. Solder Resistance	at $260 \pm 5^\circ\text{C}$ for $10 \pm 2\text{sec.}$ immerse body into solder $1/16" \pm 1/32"$	MIL-STD-750D METHOD-2031
2. Solderability	at $245 \pm 5^\circ\text{C}$ for 5 sec.	MIL-STD-202F METHOD-208
3. High Temperature Reverse Bias	$V_R = 80\%$ rate at $T_J = 150^\circ\text{C}$ for 168 hrs.	MIL-STD-750D METHOD-1038
4. Forward Operation Life	Rated average rectifier current at $T_A = 25^\circ\text{C}$ for 500hrs.	MIL-STD-750D METHOD-1027
5. Intermittent Operation Life	$T_A = 25^\circ\text{C}$, $I_F = I_O$ On state: power on for 5 min. off state: power off for 5 min. on and off for 500 cycles.	MIL-STD-750D METHOD-1036
6. Pressure Cooker	$15P_{SIG}$ at $T_A = 121^\circ\text{C}$ for 4 hrs.	JESD22-A102
7. Temperature Cycling	-55°C to $+125^\circ\text{C}$ dwelled for 30 min. and transferred for 5min. total 10 cycles.	MIL-STD-750D METHOD-1051
8. Forward Surge	Peak Forward Current	MIL-STD-750D METHOD-4066-2
9. Humidity	at $T_A = 85^\circ\text{C}$, RH=85% for 1000hrs.	MIL-STD-750D METHOD-1021
10. High Temperature Storage Life	at 175°C for 1000 hrs.	MIL-STD-750D METHOD-1031